

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
30V	27mΩ@10V	5.6A
	29mΩ@4.5V	
	45mΩ@2.5V	

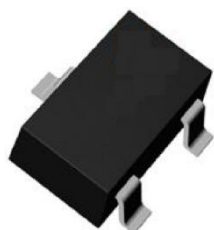
### Feature

- Trench Power MV MOSFET technology
- High Speed switching

### Application

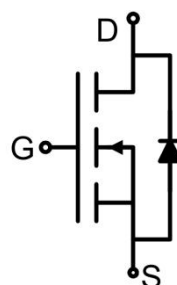
- PWM application
- Load switch

### Package

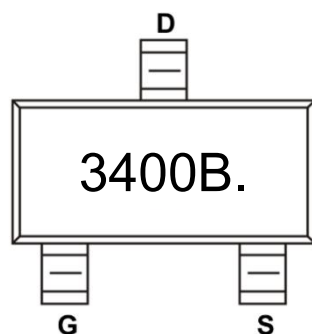


SOT-23

### Circuit diagram



### Marking



### Absolute maximum ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	5.6	A
Continuous Drain Current (T <sub>A</sub> =100°C)	I <sub>D</sub> (100°C)	3.5	A
Pulsed Drain Current <sup>1)</sup>	I <sub>DM</sub>	40	A
Power Dissipation <sup>2)</sup>	P <sub>D</sub>	1	W
Thermal Resistance Junction-to-Ambient <sup>3)</sup>	R <sub>θJA</sub>	125	°C/W
Operating Junction Temperature	T <sub>J</sub>	-55 ~ +150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

### Electrical characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V			±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.65	0.9	1.5	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.6A		20	27	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3A		22	29	
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3A		30	45	
<b>Dynamic characteristics<sup>4)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz		610		pF
Output Capacitance	C <sub>oss</sub>			60		
Reverse Transfer Capacitance	C <sub>rss</sub>			50		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.6A		16		nC
Gate-Source Charge	Q <sub>gs</sub>			2.4		
Gate-Drain Charge	Q <sub>gd</sub>			2		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.6A R <sub>G</sub> = 3Ω		6		nS
Turn-on rise time	t <sub>r</sub>			28		
Turn-off delay time	t <sub>d(off)</sub>			16		
Turn-off fall time	t <sub>f</sub>			12		
<b>Source-Drain Diode characteristics</b>						
Diode Forward Current	I <sub>S</sub>				5.6	A
Diode Forward voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 5.6A			1.2	V
Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> = 5.6A, di/dt = 100A/us		8.5		nS
Reverse Recovery Charge	Q <sub>rr</sub>			4.5		nC

Notes:

- 1) Repetitive rating; pulse width limited by max. junction temperature.
- 2) P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.
- 3) The value of R<sub>θJA</sub> is measured with the device mounted on the minimum recommend pad size, in the still air environment with T<sub>A</sub> = 25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 4) Guaranteed by design, not subject to production testing.

## Typical Characteristics

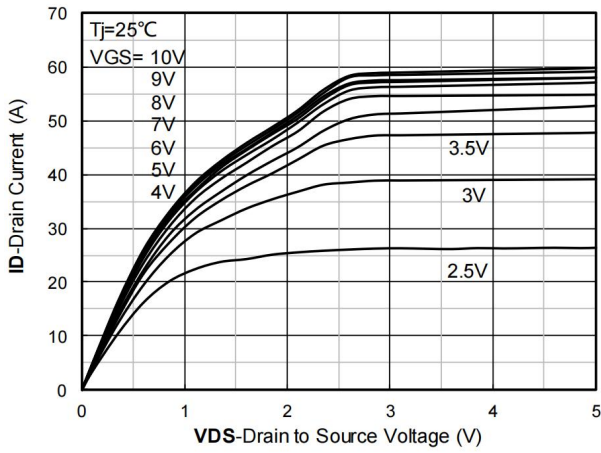


Figure 1. Output Characteristics

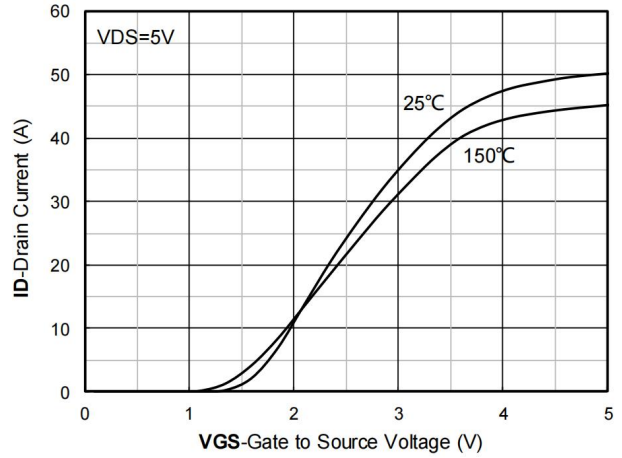


Figure 2. Transfer Characteristics

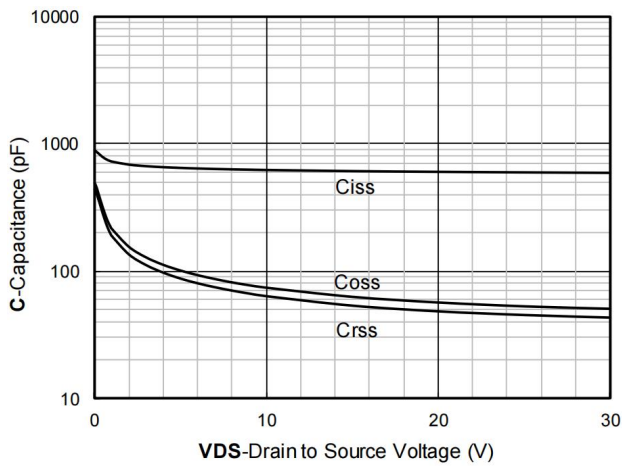


Figure 3. Capacitance Characteristics

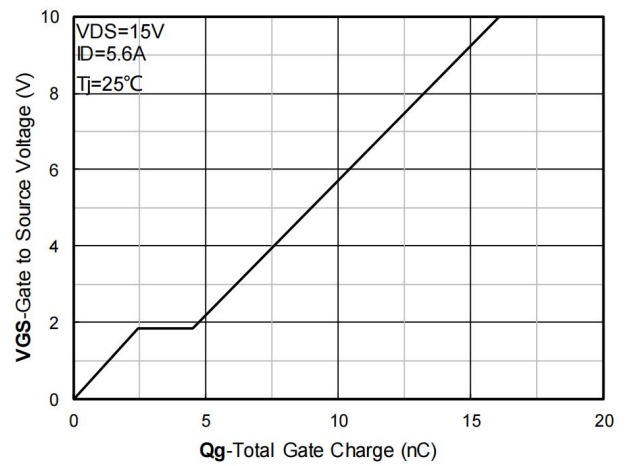


Figure 4. Gate Charge

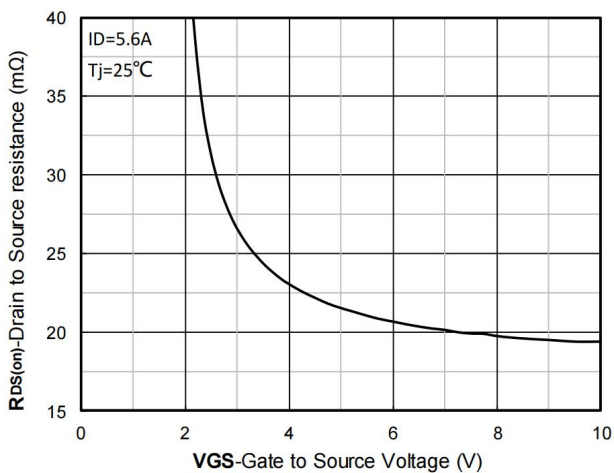


Figure 5. On-Resistance vs Gate to Source Voltage

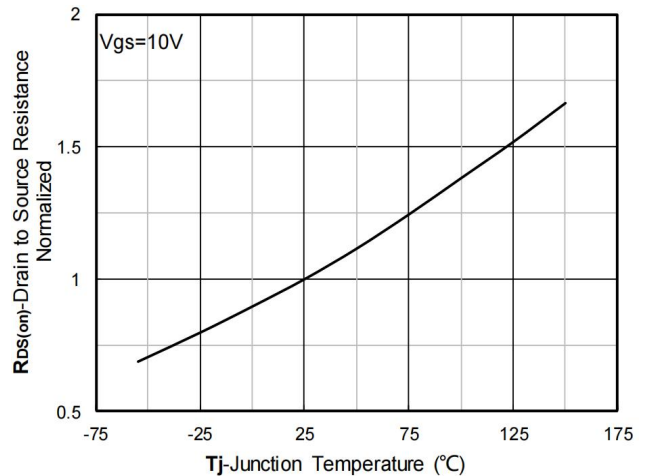


Figure 6. Normalized On-Resistance

## Typical Characteristics

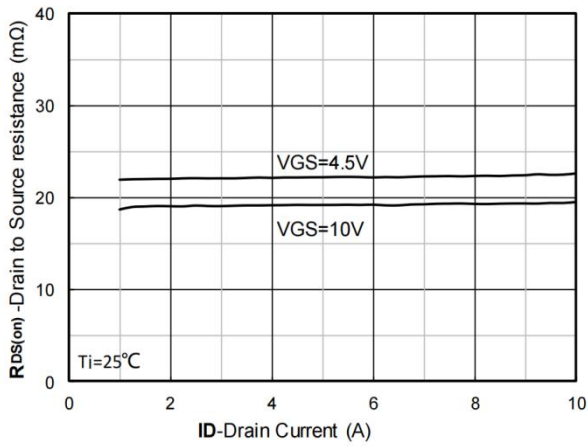


Figure 7. RDS(on) VS Drain Current

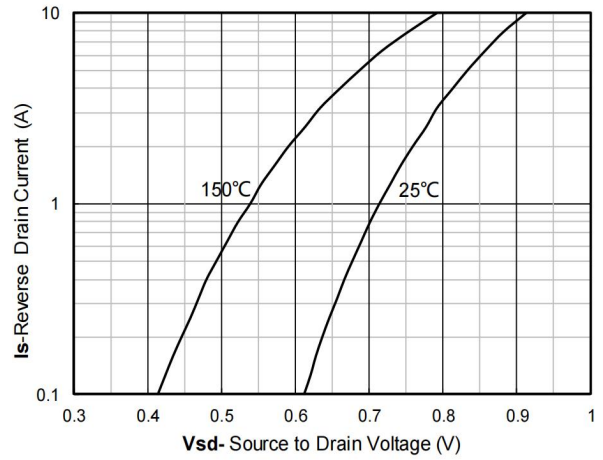


Figure 8. Forward characteristics of reverse diode

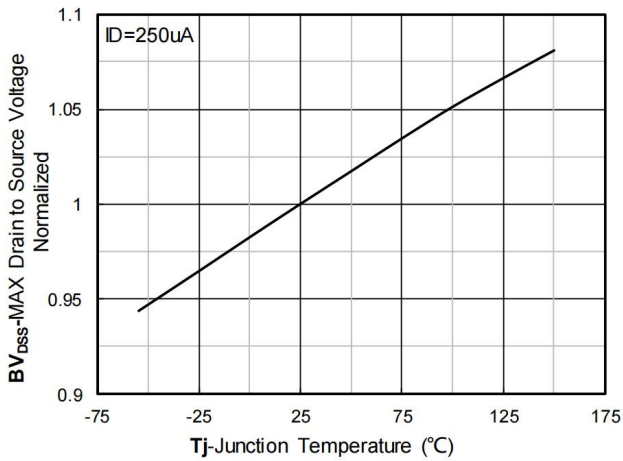


Figure 9. Normalized breakdown voltage

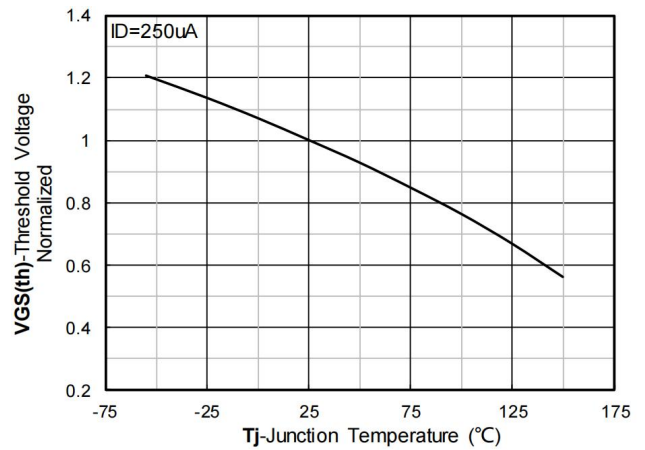


Figure 10. Normalized Threshold voltage

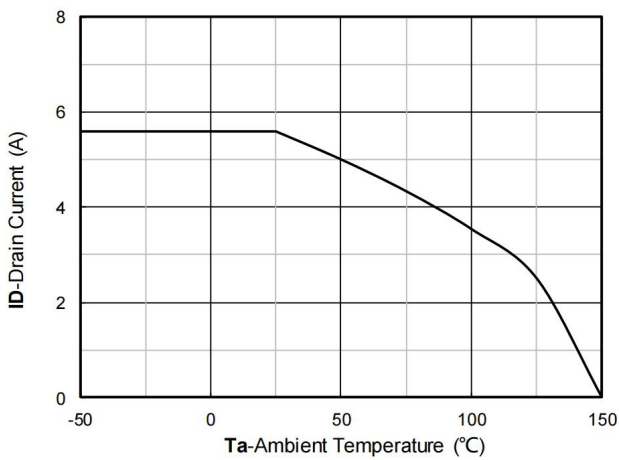


Figure 11. Current dissipation

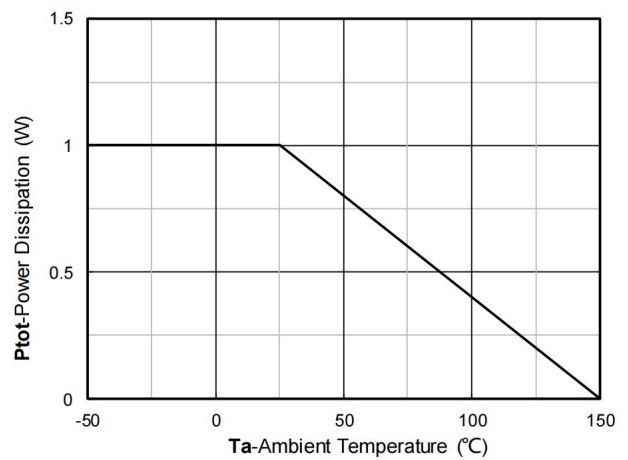


Figure 12. Power dissipation

## Typical Characteristics

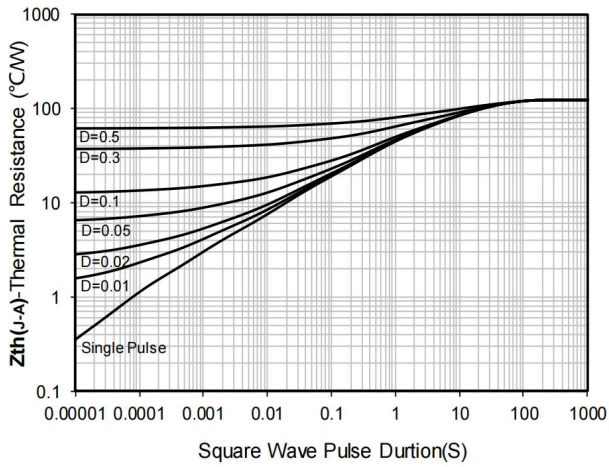


Figure 13. Maximum Transient Thermal Impedance

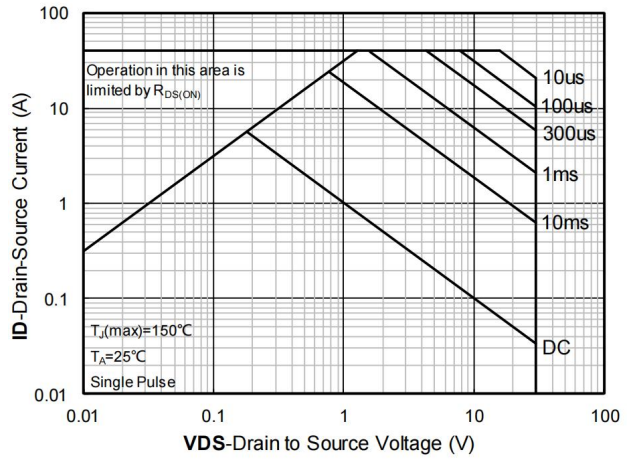
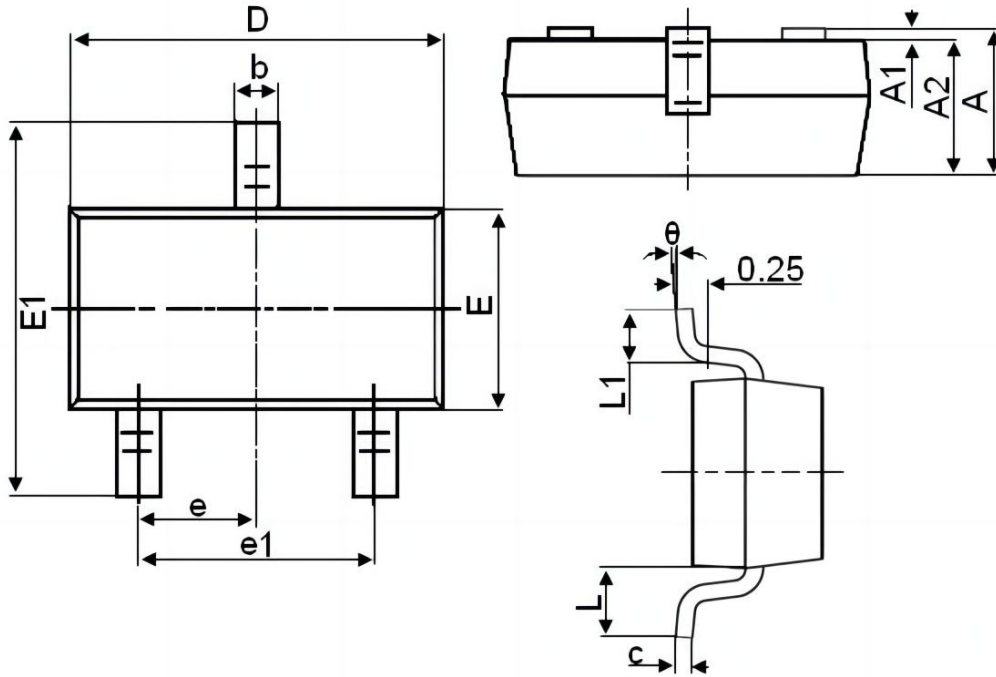


Figure 14. Safe Operation Area

### SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.200	0.003	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 REF.		0.037 REF.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	8°